

Tailored Fabrication of 3D Nanopores Made of Dielectric Oxides for Multiple Nanoscale Applications

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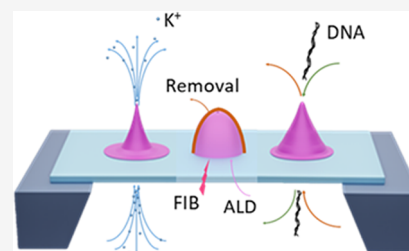
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Supporting Information

ABSTRACT: Solid-state nanopores are a key platform for single-molecule detection and analysis that allow engineering of their properties by controlling size, shape, and chemical functionalization. However, approaches relying on polymers have limits for what concerns hardness, robustness, durability, and refractive index. Nanopores made of oxides with high dielectric constant would overcome such limits and have the potential to extend the suitability of solid-state nanopores toward optoelectronic technologies. Here, we present a versatile method to fabricate three-dimensional nanopores made of different dielectric oxides with convex, straight, and concave shapes and demonstrate their functionality in a series of technologies and applications such as ionic nanochannels, ionic current rectification, memristors, and DNA sensing. Our experimental data are supported by numerical simulations that showcase the effect of different shapes and oxide materials. This approach toward robust and tunable solid-state nanopores can be extended to other 3D shapes and a variety of dielectrics.

KEYWORDS: solid-state nanopores, 3D fabrication, single-molecule sensing, memristors, ICR



Over recent decades, key advancements in nanopore technology have paved the way for improved applications in various fields, including sequencing,¹ biosensing,^{2,3} nanofluidics,⁴ ion transport⁵ and selectivity,⁶ electro-osmosis,⁷ energy harvesting,^{8–10} and electronic devices.^{11,12} Notably, nanopores offer direct physical access to biomolecule analysis^{13,14} and play a pivotal role in third-generation sequencing¹⁵ and DNA data storage.¹⁶ However, challenges persist in nanopore technology, including limited pore lifetime and stability,¹⁷ difficulties in tuning pore size,¹⁸ limited selectivity, and scalability from single pores to pore array configurations. Solid-state nanopores,^{19,20} in particular, have become the focus in single-molecule sensing due to their high robustness and durability,²¹ even under harsh conditions in terms of temperature, pressure, and pH. Various fabrication approaches have been developed,²² utilizing a wide range of materials, wherein the shape and size of the nanopores are defined by the fabrication method.⁸

The geometric distribution of charges inside the nanopore, determined by the surface charge of the material and by the 3D shape of the nanochannel,^{23,24} can have important effects on the nanopore's functionality. Depending on the shape and material of the nanopore, the inner surface charges influence the ion concentration and electrostatic potential inside the nanopore.²⁵ This leads to ionic current rectification (ICR),^{26,27} with highly asymmetric nanopores producing high ICR ratios.²⁸ Moreover, the nanopore conductance can depend on the behavior of the surface charges that redistribute within the nanopore channel due to the finite mobility of ions under

applied potentials,^{29,30} which leads to memristive behavior, as discussed in some recent works.^{31,32}

The choice of material and geometry can also influence the noise in nanopore ionic current measurements.^{19,33,34} For example, quartz nanopipettes have been employed to measure the current blockade of geometrical features separated only by 6 nm along a DNA strand,³⁵ attributing this super-resolution to the enhancement of the electric field at the tip of the nanopore. However, a quartz nanopipette limits the application to a single nanopore. On the contrary, nanopores on a silicon chip³⁶ can be fabricated as nanopore arrays³⁷ for parallel and high-throughput applications. In this view, HfO₂ (hafnium dioxide) step-like conical nanopore arrays on Si₃N₄ membranes have been recently fabricated for biosensing and energy harvesting, using a modified atomic layer deposition (ALD) configuration.⁸ Taking inspiration from this work, we present a robust method to fabricate three-dimensional on-chip nanopores with arbitrary geometries made of different dielectric oxides. These structures can be readily realized on solid-state substrates (on-chip) and fabricated as single pores, as pore arrays, or in arbitrary arrangements. The fabrication is based on focused ion beam (FIB) lithography that produces a hollow

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conical structure of a photoresist mold onto a silicon/silicon nitride chip.³⁸ Then the metal oxide is deposited from the back side of the membrane by ALD or physical vapor deposition (PVD).³⁹ The crucial step is the full removal of the hardened photoresist that we achieved by UV light exposure (to break the cross-linking of the polymer chain in the resist) followed by low-power oxygen plasma in our reactive ion etching with inductively coupled plasma (ICP-RIE) setup or by heating the samples to 600 °C under an O₂ atmosphere. With this process, we obtain nanopores with few nanometer apertures consisting only of the metal oxide, while their shape can be controlled in 3D by FIB lithography.⁴⁰ We demonstrate the fabrication of nanopores from four different oxides (SiO₂, Al₂O₃, TiO₂, and HfO₂) and three different shapes (with concave, convex, or straight edge profiles) and investigate their performance in ICR and single-molecule detection and as ionic memristors.^{39,27}

Figure 1 depicts the three different conical nanopore shapes fabricated on a silicon nitride membrane that we discuss in this

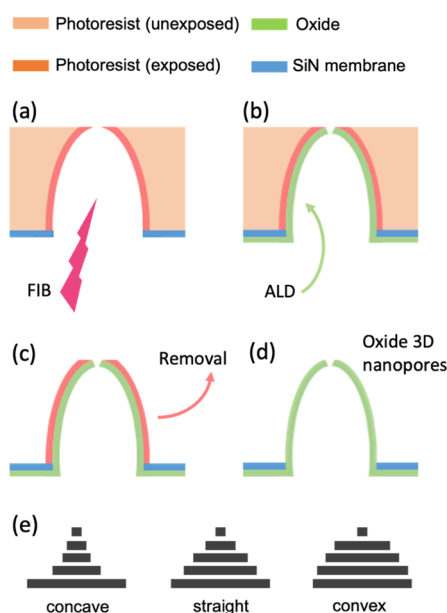


Figure 1. 3D oxide nanopore fabrication illustrated in cross-sectional schemes. (a) A photoresist layer on a SiN membrane is milled by FIB lithography from the backside, resulting in a thin layer of hardened resist. The oxide material is deposited by ALD as a thin layer (b), and then the photoresist is removed using standard solvents (c) leaving the hardened layer behind, which is removed by UV exposure and oxygen plasma or thermal annealing at high temperature (d). (e) Different nanopore shapes are obtained by concentric disk exposure in the FIB lithography.

work. The fabrication process is described in Figures S1 and S2, and scanning electron microscope (SEM) images of the differently shaped 3D nanopores are shown in Figure 2. We report several additional examples of single nanopores and nanopore arrays in the Supporting Information in Figures S3 and S7 to demonstrate the versatility of the method. The key features are the deposition of the photoresist from the top side, with the successive FIB lithography and metal oxide deposition from the backside of the membrane. This combination retains the freedom in the design of the nanopore of the FIB lithography and enables the full removal of the photoresist mold after metal oxide deposition. An additional advantage of the approach is that the nanopore aperture can be defined with

nanometer resolution by the fine thickness control of the ALD of the dielectric metal oxide. To fabricate 3D hollow conical structures with different edge profiles in the photoresist, we adapted a technique based on FIB milling of concentric disks with different diameters; see Figure S2 for details.^{38,41,42} Here the secondary radiation and electron scattering related to the ion-beam exposure results in cross-linking of the photoresist in the vicinity of the removed disk volume, which leads to a layer of hardened photoresist with ca. 50 nm thickness that wraps the external shape of the disk stacks. This photoresist mold is then used as a template for the dielectric oxide nanopores.

We note that we distinguish here two different photoresist thicknesses: one is the overall layer thickness after spin coating in the micrometer range, defining the height of the 3D-nanopore; the other is the thickness of the cross-linked photoresist layer. The metal oxide can be deposited by PVD or ALD. PVD can be directly applied to the samples since the process is directional and therefore covers only the backside of the membrane and the photoresist cones. However, PVD films are slightly grainy, and therefore, this approach provides only limited control on the nanopore diameter, with the risk of blocking the opening. With ALD, very homogeneous layers with high control on thickness can be obtained,⁴⁰ but it is important to ensure one-sided deposition to be able to remove the photoresist mold. To achieve this, we place the sample top side down on a polydimethylsiloxane (PDMS) substrate that adheres to the photoresist and protects the top side from the ALD, while leaving the backside accessible for metal oxide deposition. Thermal ALD is preferred over plasma ALD, as it produces higher quality oxide layers^{43,44} and does not contribute to further hardening of the photoresist that would make the resist removal more difficult.

The removal of the hardened photoresist mold is challenging.^{45,46} Standard oxygen plasma processes do not work, as they only reduce the thickness⁴⁵ to a persistent layer of around 30 nm.⁴⁷ Solvents such as *N*-methyl-2-pyrrolidone (NMP), designed to remove hardened photoresist, prove ineffective in the complete elimination of this layer. We tested piranha solution as an additional etchant, but this resulted in membrane damage, and aggressive oxygen plasma treatments performed in an RIE-ICP configuration led to damage of the thin dielectric layers. We found that resist removal using UV light to break the cross-linking in the photoresist^{45,47} followed by low-power oxygen plasma in an ICP-RIE leads to fast and effective removal of the photoresist. Another successful strategy that we applied for resist removal is thermal annealing at 650 °C in the presence of oxygen, which facilitates the decomposition and degassing of organic materials⁴⁸ and concurrently improves the mechanical and optical properties of the oxide layer.^{49,50} Both methods proved to be effective in fully removing the hardened photoresist layer, as confirmed by the EDS mapping shown in Figure 2e–g.

The metal deposition by ALD on a mold gives access to a wide variety of dielectric oxides as materials for 3D nanopores. We tested all materials available in our ALD system, which are SiO₂, Al₂O₃, TiO₂ (titanium dioxide), and HfO₂; see Figure 2 and Figures S6 and S7 in the SI. This set of dielectric oxides outlines the flexibility of our fabrication that allows selecting the nanopore material to meet specific application requirements, in particular toward high dielectric constant materials that can open up possibilities to integrate nanophotonic resonators and Mie-tronics in the nanopore platform.^{51,52}

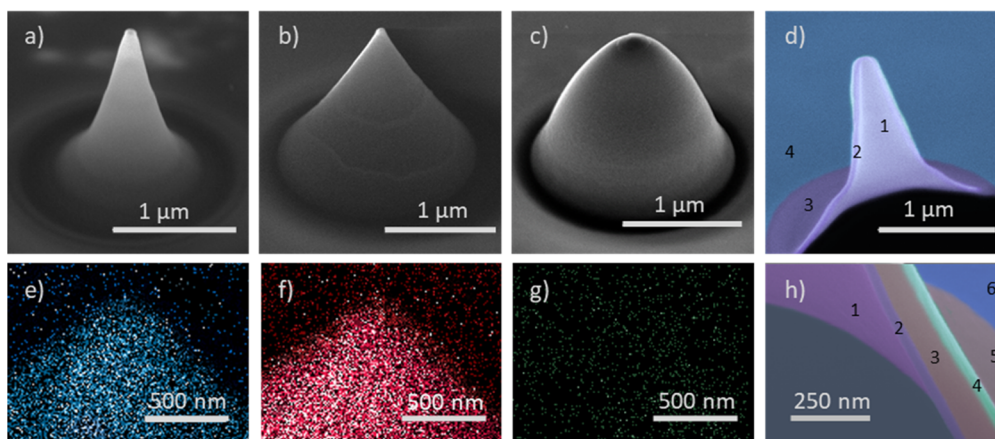


Figure 2. Electron microscopy analysis of metal oxide nanopores with different shapes. SEM micrographs of Al_2O_3 nanopores with concave (a), straight (b), and convex (c) edge profiles. The aperture of the nanopores is around 30 nm in all cases. (d) Cross section of a concave Al_2O_3 nanopore (marked 1, interior wall of the nanopore in SiO_2 ; 2, cross section of the dielectric wall; 3, outer SiO_2 wall; 4, Si_3N_4 membrane). (e–g) Compositional analysis of an Al_2O_3 nanopore by electron dispersive spectroscopy (EDS) mapping, showing the signals for Al (e), O (f), and C (g). (h) Cross section of a convex SiO_2 nanopore before photoresist removal; the SiO_2 and photoresists section are highlighted by false colors (marked 1, interior wall of the nanopore in SiO_2 ; 2, cross section of the dielectric wall; 3, cross section of the photoresist wall; 4, Pt layer; 5, outer photoresist wall; 6, Si_3N_4 membrane).

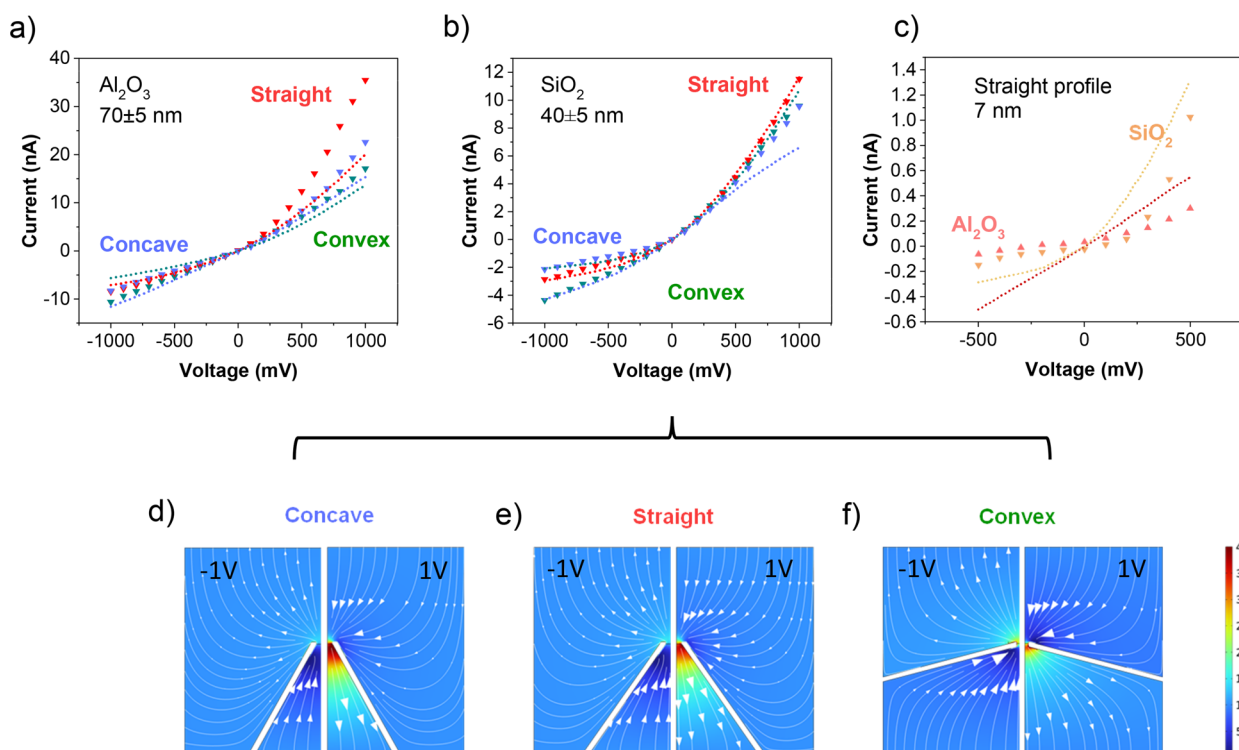


Figure 3. Ionic current rectification: measured (triangles) and simulated (dotted lines) I – V characteristics of the three nanopore geometries in a 10 mM KCl electrolyte. (a–c) Current voltage curves for nanopores with different shapes and materials as described in the legends. (d–f) Simulated concentration profiles of K^+ [mol/m^3] and total flux (streamlines) for a SiO_2 nanopore with 40 nm diameter with (d) concave, (e) straight, and (f) convex profile.

Now we turn to explore the properties and functionality of the all-dielectric oxide nanopores in a range of applications, which are ICR, single-molecule detection, and as memristors. In this respect, we take advantage of the design freedom that our fabrication provides and investigate the impact of the different oxide materials (SiO_2 , Al_2O_3), different nanopore shapes (with concave, convex, and straight profiles), and pore diameters (ranging from 7 to 70 nm).

ICR depends on the nanopore shape, size, and surface properties.⁵³ Figure 3a shows the conductance (in 10 mM KCl electrolyte) of Al_2O_3 nanopores that have different shape, but a similar channel length of 1.4 μm and pore diameter of around 70 nm. ICR is observed for all three shapes with a higher current at positive bias with respect to negative bias, and this effect is strongest for the pores with straight profiles. We observe a similar behavior for SiO_2 nanopores with about 40 nm pore diameter, as depicted in Figure 3b. As could be

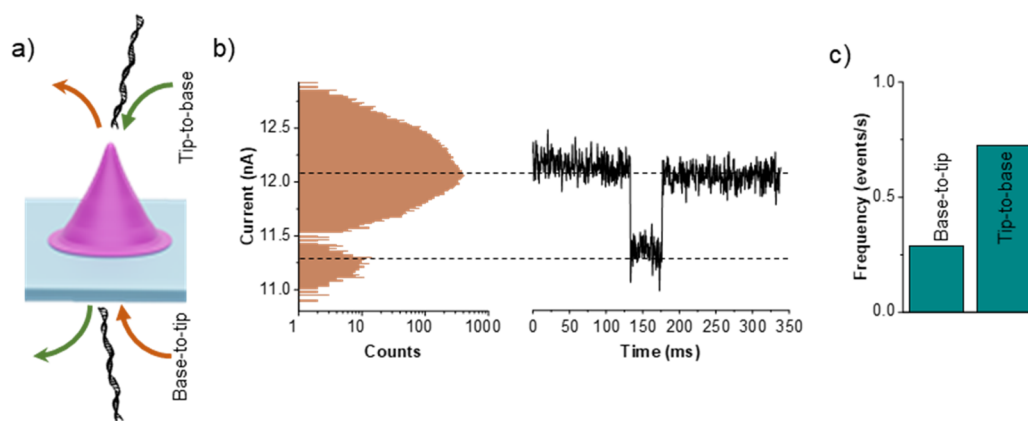


Figure 4. (a) Schematic layout of the DNA translocation experiments. (b) Current blockade histogram of λ -DNA translocations through a straight profile nanopore in 1 M KCl at $V = 500$ mV, measured at 20 kHz, with a characteristic translocation event on the right. (c) Relative frequencies of DNA translocation events in tip-to-base and base-to-tip directions.

expected, the 3D nanopores exhibit strong rectification with typical ICR ratios in the range between 4.6 and 1.6, which is significantly higher than ICR in planar pores that typically have ICR ratios around 1.

Our smallest nanopores with opening diameters of around 7 nm exhibit even stronger ICR. Figure 3c exemplifies the I - V curves for straight pore shapes fabricated with SiO_2 and Al_2O_3 . In such narrow nanopores, the movement of the ions is dominated by the surface charge; thus the rectification effects are enhanced, and we obtain ICR (at 500 mV) ratios of 7.0 for SiO_2 and 4.9 for Al_2O_3 , whereas values reported for conical nanopores in a SiO_2 membrane are in the range of 1–2.⁵⁴

To elucidate the fact that pores with straight profiles feature stronger ICR than concave or convex shapes, we performed finite element method modeling (COMSOL Multiphysics version 5.3). The Poisson–Nernst–Planck (PNP) equations^{55,56} were employed to describe distributions of electric potential and ionic species concentrations across the entire domain, as well as to simulate respective ionic fluxes. Further details can be found in Section 3 in SI. As shown in Figure 3d–f, which depicts the magnified view on the pore tip region for concave, straight, and convex geometries, the major difference between the shapes is the value of the half-cone angle in the vicinity of the opening. This angle typically reaches 15–30° for concave, 30–45° for straight, and 70–80° for convex nanopores and has a pronounced effect on local ionic distributions and ionic conductivity. As the angle of the nanopore increases from concave to straight and then to convex shapes, a corresponding reduction in the conductivity asymmetry at opposite bias polarities can be observed. This consequence of a smaller accumulation and depletion of ionic species at the tip of the nanopore at higher cone angles is related to a reduced asymmetry of the mass transport between the inner and outer parts of the nanopore. Inside the pore, the mass transport is rather restricted and allows for stronger ion accumulation or depletion (depending on bias polarity), which also strongly depends on the cone semiangle, whereas the mass transport outside the pore remains mainly unchanged. These variations in the geometry cause a major effect on ICR,^{24,57,58} with stronger mass-transport asymmetry (inside vs outside of the pore) that causes more intense high and low conductance states at opposite biases for concave, rather than straight, or even convex pore shapes.

Further differences between the fabricated nanopores are related to the magnitude of the surface charges, which are directly related to the choice of the pore material. We note that we needed to assign negative surface charges to accurately reproduce our experimental results, in contrast to other reports.⁵⁹ This difference most likely originates from impurities or structural differences induced by the deposition process that favors deprotonation of hydroxyl groups on the aluminum surface, rendering the surface negative. The surface charge can depend on the fabrication methods, chemical functionalization of the pore walls, and interactions between surface groups and ions in the electrolyte solution due to acid–base (pH) or other equilibria.^{54,60} In this regard, the main difference between Al_2O_3 and SiO_2 nanopores is in their surface charge. In our ICR simulations, we assigned surface charges from -0.02 to -0.04 C/m² and from -0.06 to -0.1 C/m² for SiO_2 and Al_2O_3 nanopores, respectively, thus resulting in a different degree of ICR. Therefore, the nanopore fabrication concept developed in this work offers a versatile platform to manipulate ICR in a wide range of conditions, from geometry to nanopore materials.

Figure 4 reports the properties of the nanopore in single-molecule sensing, implemented by electrical detection of the translocation of single λ -DNA molecules in 1 M KCl solution through the nanopore in a nanopore reader.⁶¹ The conical shape improved the overall signal-to-noise ratio compared to our previous work⁶² with cylindrical nanopore geometry. The conical shape resulted also in an asymmetry as compared to the direction of translocation in terms of both frequency of events and signal-to-noise; that is, the relative signal was $\Delta I/I_0 = 8\%$ for base-to-tip and $\Delta I/I_0 = 11\%$ for tip to base translocations (Figure 4a), and we observed approximately twice the amount of translocation events in the tip-to-base direction with respect to the base-to-tip direction (Figure 4c). This is in agreement with recent results reported in glass nanopipets³⁵ and HfO_2 step-like conical nanopores and most likely originates from the nonuniform electric field distribution and the electroosmotic flow that the DNA molecule must overcome in the translocation process.⁸

Ionic memory resistors (memristors) promise groundbreaking advancements in neuromorphic technologies^{63–65} by exploiting their capability to unite computing and memory in the same element. The conductance of ionic memristors at a given bias voltage depends on the preceding voltage bias

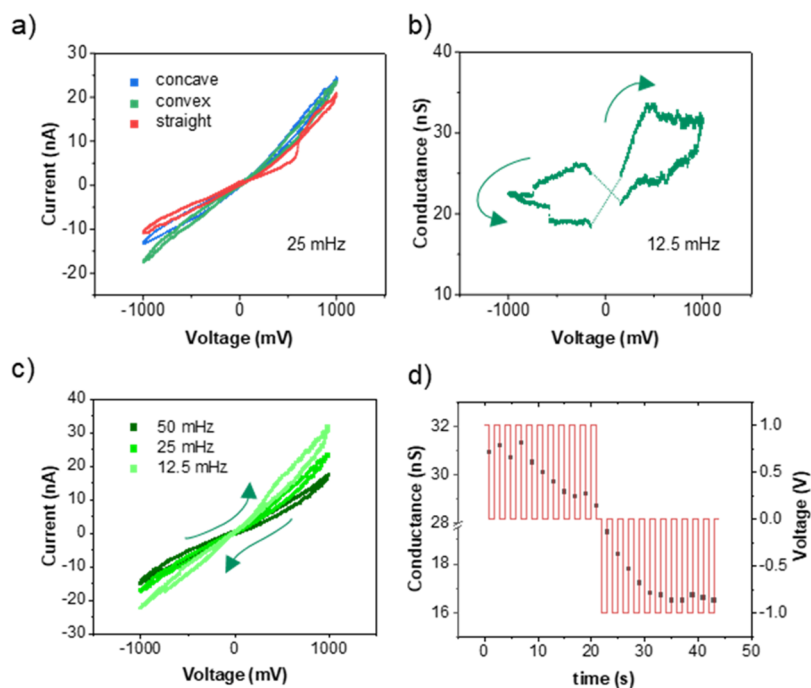


Figure 5. (a) Memristive behavior of the SiO₂ 3D nanopores during cyclic ramp voltammetry in a 200/20 mM (tip side/base side) KCl gradient. (b) Conductance of a conical pore of convex profile, showing the typical crossing of unipolar pores. The conductance curve is such that it decreases when the applied voltage increases; switching behavior occurs when the sign of the voltage is changed. (c) Memristive response depending on the cycling frequency. Here we show that the area of the hysteresis loop of a conical pore of the convex profile increases with lower cycling frequencies. (d) Change in the conductivity (black) of the 50 nm concave pore as a series of 1 s voltage pulses (red) is applied. These pores show a “learning” behavior, where the conductivity decreases as more pulses are applied.

events; that is, the conductance bears memory of the recent history of bias voltages across the ionic memristor. This memory effect observed in memristors is reminiscent of short-term synaptic plasticity in neurons, where the response of a neuron after a synapse depends on the history of the activations before the synapse.^{66,67}

Figure 5 reports the I – V curves of cyclic voltammetry in conical 3D nanopores. These plots show the pinched hysteretic behavior that is the fingerprint of memristors.⁶⁸ Figure 5a shows the hysteretic behavior of the three types of conical pores. Although there are significant differences between shapes, we observe qualitatively the same behavior with an open hysteresis loop in the I – V (Figure 5a) that leads to a crossing at around zero bias voltage in the conductance–voltage curve (Figure 5b). This memristive behavior is similar to that reported in the literature for larger, concave pores,^{12,69} and its origin stems from the transient concentration polarization that is due to the asymmetry of the pores, their conical shapes, and their charged surfaces. Significant theoretical work has been done to estimate the diffusion limited memory time scale of the hysteretic loop, which should scale as $\frac{L^2}{D}$, where L is the channel length of the pore and D the ionic diffusivity coefficient.^{70,71} Using $L = 1.4 \mu\text{m}$ and $D = 1.4 \frac{\mu\text{m}^2}{\text{ms}}$ yields time scales on the order of milliseconds, thus orders of magnitude faster than the behavior that we observe in Figure 5c,d that is in the range of several tens of seconds. We therefore think that the trapping and detrapping of surface charges in the channel are at the origin of the memristive behavior that we observe.

As an additional characterization of the memristor behavior, we show, in Figure 5d, an experiment in which the nanopores

are subjected to a series of positive voltage pulses followed by negative ones. The pulses produce a synaptic-like decrease of the conductance for both positive and negative pulses, consistent with a unipolar memristor. This means that the nanopore effectively “remembers” the previous pulses and that its downstream conductance can be “programmed” by providing an appropriate train of pulses. This behavior suggests that nanopores of this kind could be employed as elements of nanofluidic neuromorphic circuits.

In conclusion, we reported a fabrication route that allows nanopores with different conical shapes to be obtained that consist fully of dielectric oxides. This is a key advancement in terms of nanopore shape and material, since it avoids typical shortcomings of polymer nanopores, which are contamination of the analytes, low stability under harsh conditions and over long-time scales, and low refractive index and dielectric constant that result in lower performance in optics and electronics. In this sense, our approach integrates the advantages of glass-pipette nanopores that are only available on the macroscale to on-chip technologies that enable parallel processing by microarrays of nanopores and their integration in microfluidics. The chemical robustness and high dielectric constant of the metal oxides that are available for ALD also open the way to integrate nanoplasmonics⁷² and Mie-tronics with such an on-chip nanopore platform. We demonstrated the excellent properties of the conical dielectric oxide nanopores in ionic current rectification, where they allowed reaching high rectification ratios even for relatively large pore diameters of 50–70 nm, and finite element method simulations elucidated the shape effects on the ionic current flow. We further demonstrated improved performance in electrical detection of DNA translocation of the conical nanopores compared to

cylindrical ones and connected the asymmetry in ionic current flow and conductance to the hysteresis that we observed in cyclic voltammetry. These insights showed that asymmetric shapes such as concave and convex nanopores are favorable for achieving hysteresis and memristive behavior, which allows designing nanopores for ionic memristor devices that have the best possible properties for the targeted applications, for example, in neuromorphic computing. Therefore, our work opens up new possibilities for exploring the physics and applications of conical nanopores, such as sensing,⁷³ sequencing,^{74,75} nanofluidics,⁷⁶ nanoelectronics,⁷⁷ and energy harvesting.⁷⁸ With the addition of a metallic layer, the versatility of our method allows for the design of tunable plasmonic antennas for enhanced optical techniques.^{72,79} Furthermore, exploiting the ability to fabricate 3D nanopores in different materials with high refractive index paves the way to the design and integration of all dielectric nanoresonators, extending the applications of 3D nanopores into Micronics.^{80,81}

■ ASSOCIATED CONTENT

SI Supporting Information

The Supporting Information is available free of charge at <https://pubs.acs.org/doi/10.1021/acs.nanolett.4c02117>.

Section 1: Nanopore Fabrication and Nanopores from Different Materials; Section 2: Electrical Measurement Details; Section 3: Simulations – Details of the COMSOL modeling; Section 4: Methods and Materials (PDF)

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Author Contributions

GL conceived the fabrication method, performed the fabrication, and prepared the manuscript, AS and DM performed the numerical simulations, AD, SW, GP, and AG performed the memristor characterization, and RK and DG supervised the work.

Notes

The authors declare no competing financial interest.

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